Electronic Supplementary Information

Electrical transport and mechanical properties of thermoelectric tin selenide

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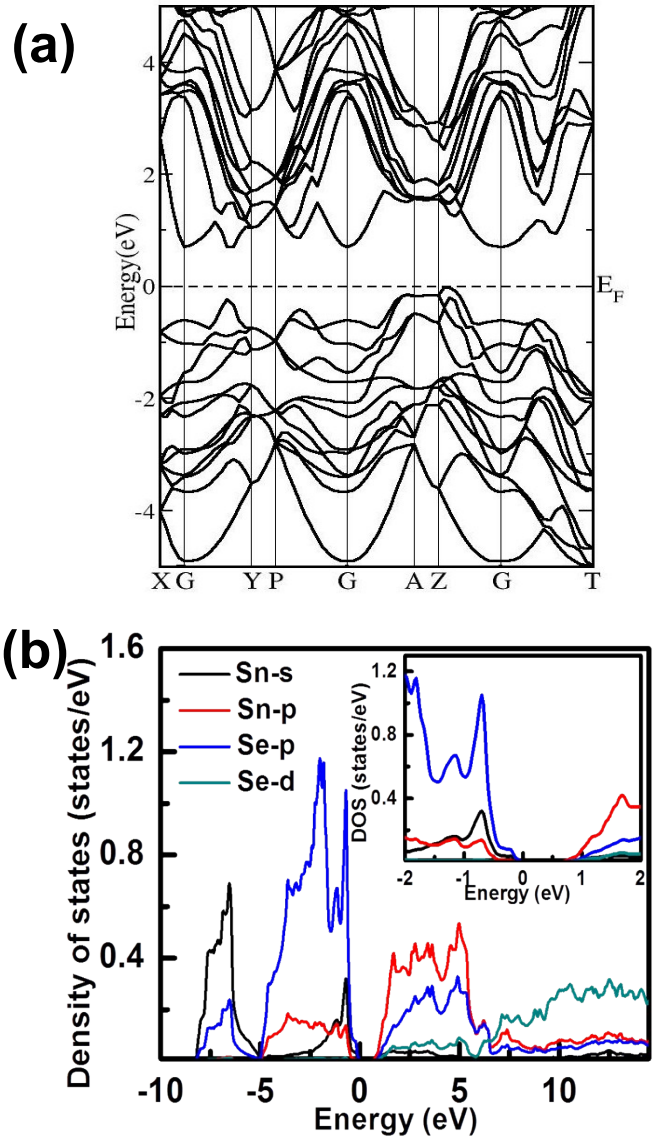

Figure S1: (a) Electronic band structure of *Pnma*-phase of SnSe. Fermi level is indicated by E_F. The crystal structure used to carry out DFT calculations is orthorhombic. The top of valence and lies along Z – Γ direction while bottom of conduction band is located at Γ point yielding an indirect band gap of 0.74 eV. (b) Partial density of states for *Pnma*-phase of SnSe.

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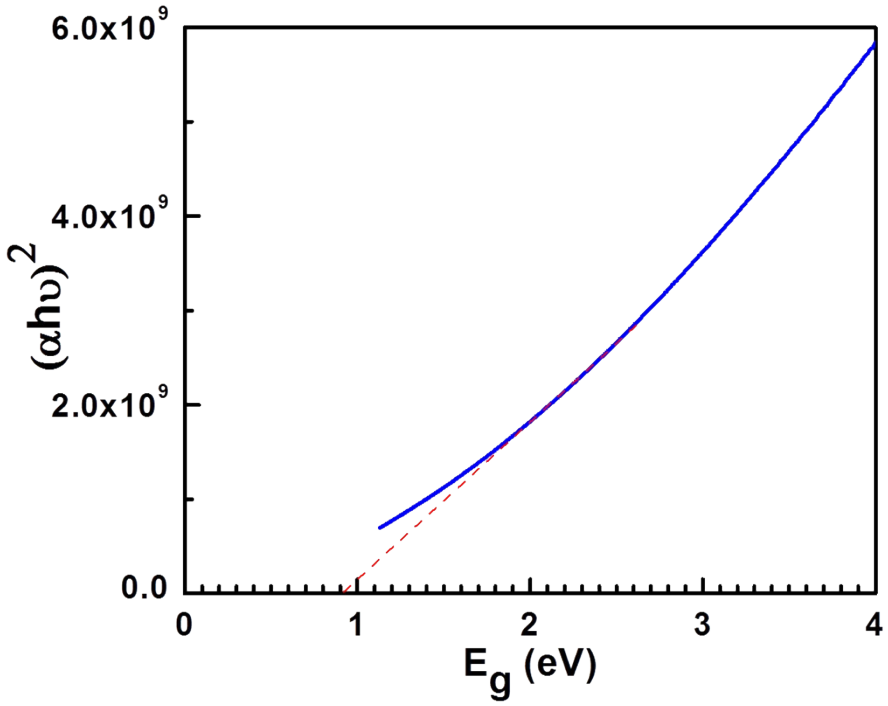

Figure S2: Band gap calculation of SnSe (*Pnma*) from UV absorption spectra.

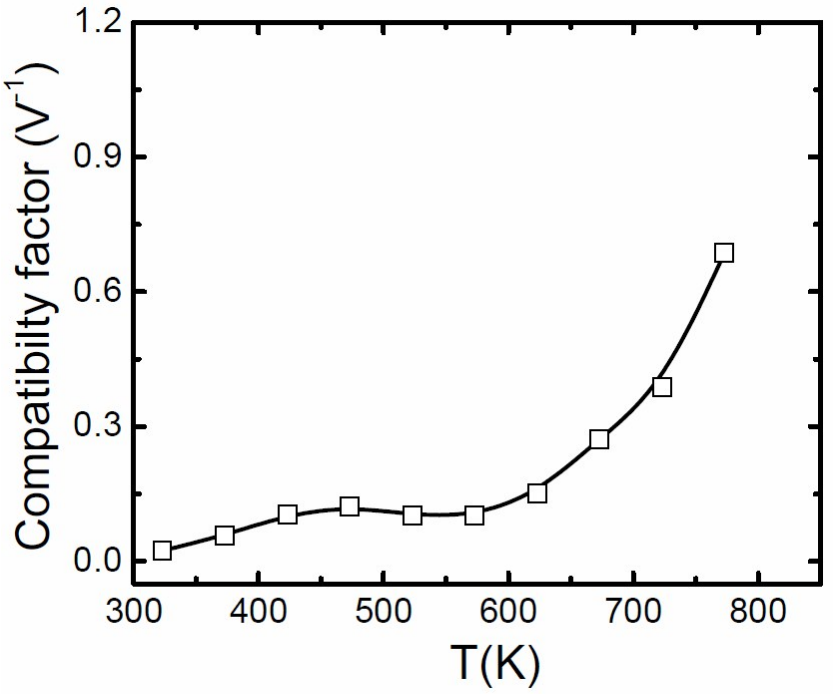

Figure S3: Temperature dependence of thermoelectric compatibility factor of as-synthesized p-type SnSe.